



Thyristor Modules

SKET 800

Features

- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

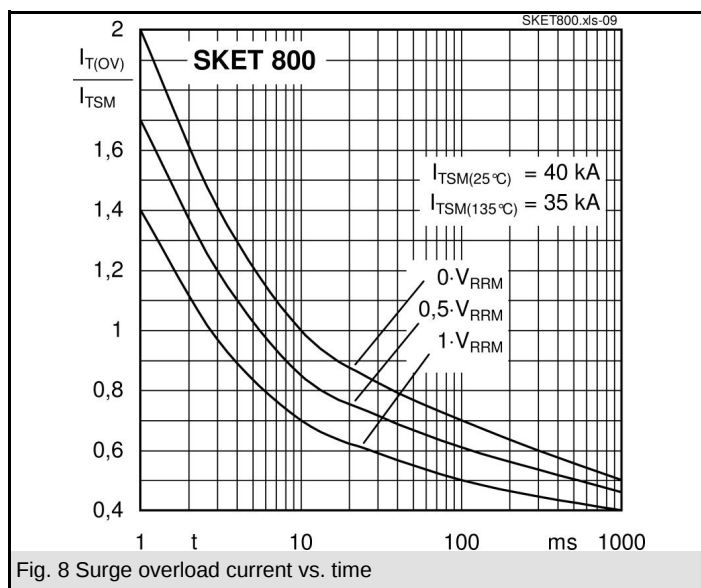
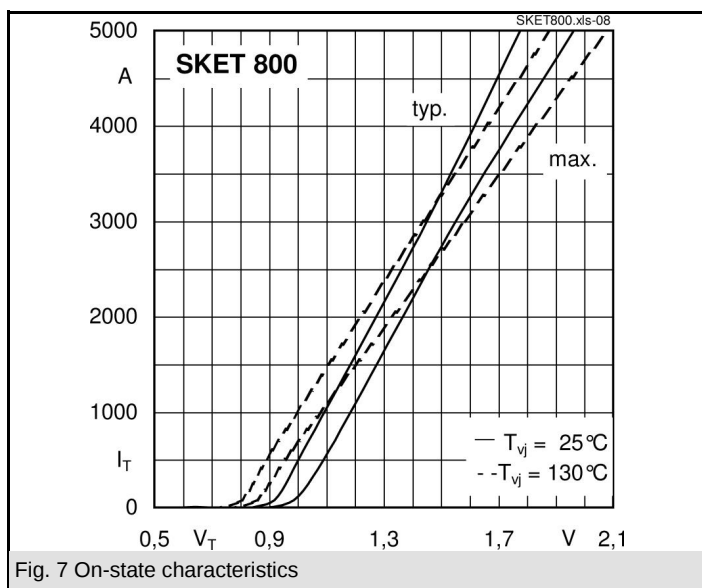
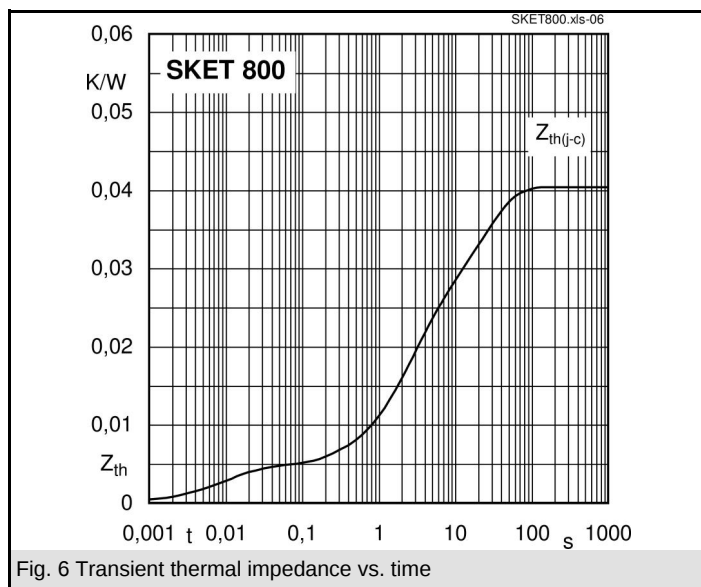
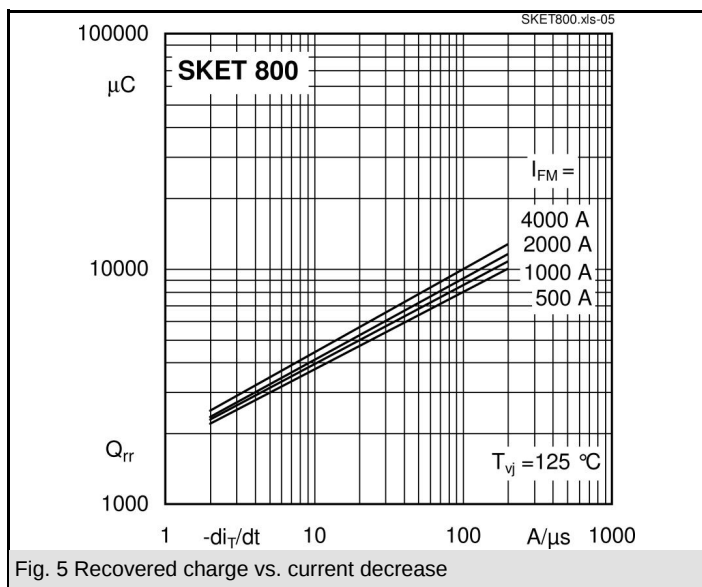
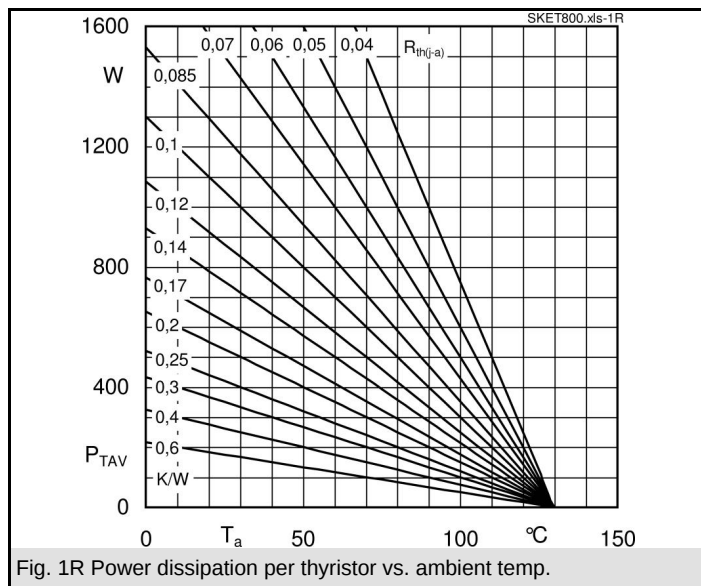
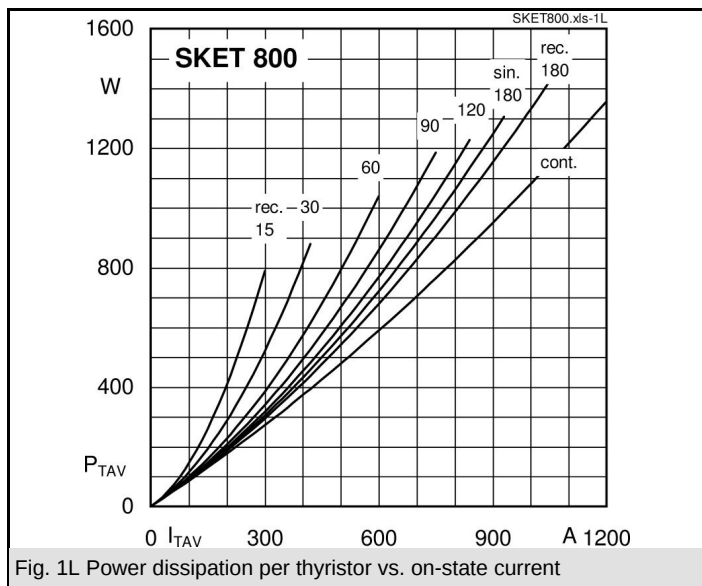
- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Softstart application

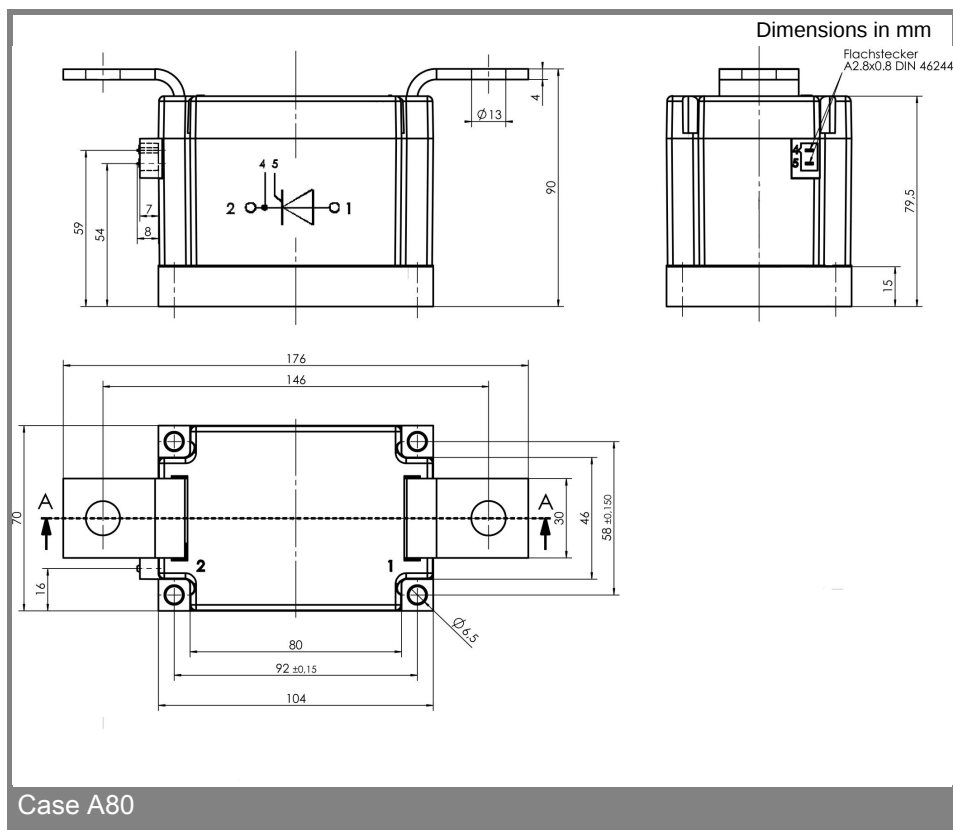
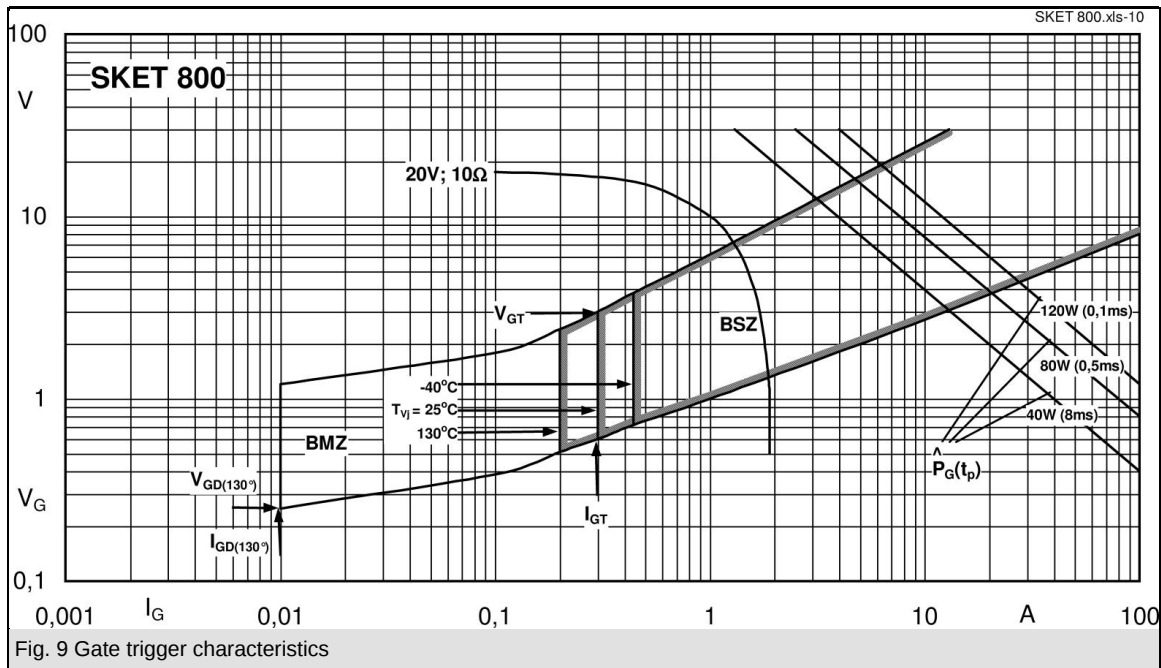
- 1) calculated with characteristic values
2) characteristic values

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 1500$ A (maximum value for continuous operation) $I_{TAV} = 805$ A (sin. 180; $T_c = 85$ °C)		
1500	1400	SKET 800/14G H4		
1900	1800	SKET 800/18G H4		

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	805 (595)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	37000	A
	$T_{vj} = 130$ °C; 10 ms	32000	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	6485000	A²s
	$T_{vj} = 130$ °C; 8,3 ... 10 ms	5120000	A²s
V_T	$T_{vj} = 25$ °C; $I_T = 3000$ A	max. 1,55	V
$V_{T(typ.)}^{2)}$	$T_{vj} = 25$ °C; $I_T = 3000$ A	1,45	V
$V_{T(TO)}$	$T_{vj} = 130$ °C	max. 0,83	V
r_T	$T_{vj} = 130$ °C	max. 0,25	mΩ
$V_{T(TO)(typ.)}^{2)}$	$T_{vj} = 130$ °C	0,78	V
$r_{T(typ.)}^{2)}$	$T_{vj} = 130$ °C	0,22	mΩ
I_{DD}, I_{RD}	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 150	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 \cdot V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 130$ °C	max. 200	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 130$ °C	max. 2000	V/μs
t_q	$T_{vj} = 130$ °C	200	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	1000 / 2000	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	1500 / 2500	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 300	mA
V_{GD}	$T_{vj} = 130$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 130$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.	0,0405	K/W
$R_{th(j-c)}$	sin. 180	0,042	K/W
$R_{th(j-c)}$	rec. 120	0,043	K/W
$R_{th(c-s)}$		0,01	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1s / 1 min.	4800 / 4000	V~
M_s	to heatsink	6 ± 15 %	Nm
M_t	to terminal	18 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	2150	g
Case		A80	







This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.